FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200315134-1	APPLICATION NO. 10/799,325	CONFIRMATION NO.
	APPLICANT Randy L. Hoffman		
	FILING DATE Herewith	GROUP	

REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
TT	1A	4,559,238	12/17/2985	Bujatti, et al.	
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TT	1D	2003/0047785	02/13/2003	Kawasaki, et al.	
TT	1E	2003/0104659	06/05/2003	Arakawak, et al.	
TT	1F	2003/0111663	06/19/2003	Yagi	
TT	1G	2003/0139026	07/24/2003	Lucovosky	
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TT	1I	2003/0186489	10/02/2003	Ishikawa	
TT	1J	2003/0218221	11/27/2003	Wager, III, et al.	
TT	1K	2003/0218222	11/27/2003	Wager, III, et al.	

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		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
TT	1L	WO 97-06574	02/20/1997	Cillessen, et al.		
TT	1M	EP1134811	09/19/2001	Kawasaki, et al.		
	1N					
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

TT	1Q	Aoki, Akira, et al., "Tin Oxide Thin Film Transistors", Japan J. Appl. Phys., Vol. 9, p.582 (1970).
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EXAMINER	DATE CONSIDERED
Thien Tran	10-11-2005

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TT	2A	2003/0224550	12/04/2003	Kokubo, et al.	
TT	2B	60/490,239	07/25/2003		Transparent Thin Film Transistor with Zinc-Tin Oxide Channel...
TT	2C	10/763,239	01/23/2004		Semiconductor Device
TT	2D	10/763,354	01/23/2004		Transistor Including a Deposited Channel Region Having a ...
	2E				
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FOREIGN PATENT DOCUMENTS

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	2L					
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TT	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transistion Metal Oxides", SPIE Vol. 2697, pp. 520-527.
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	3L					
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TT	3Q	Hajnal, Zoltán, et al., "Role of oxygen vacancy defect states in the N-type conduction of B-Ga2O3", Journal of Applied Physics, Vol. 86, No. 7, pp. 3792-3796 (October 1, 1999).
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TT	4Q	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", Journal of Applied Physics, Vol. 93, No. 3, pp. 1624-1630 (February 1, 2003).
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

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TT	7Q	Ueda, Naoyuki, et al. "Anistrophy of electrical optical properties in B0Ga2O3 single crystals", Appl. Phys. Lett., Vol. 71, No. 7, pp. 933-935 (August 18, 1997).
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TT	8S	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO3 Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).

EXAMINER	DATE CONSIDERED
Thien Mai	10-11-2005

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	APPLICANT Randy L. Hoffman		
	FILING DATE Herewith	GROUP	

REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
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TT	9R	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLEAD_" Research Disclosure, p. 890 (July 1998).
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EXAMINER	DATE CONSIDERED
Thien Tran	10-11-2005

PTO/SB/08A (08-03)
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 2

Complete if Known	
Application Number	10/799325
Filing Date	Mar 12, 2004
First Named Inventor	Randy Hoffman
Art Unit	2811
Examiner Name	Thien Tran
Attorney Docket Number	200315134-1

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
TT		US- 5,744,864	04-28-1998	Cillessen	
		US-			
		US-			
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		WO 02/15233	02-21-2002	Walter		
		EP 1 306 858	~~05-02-2003~~	Japan Science		
		~~EP 1 367 657~~	12-03-2003	Koha Co.		

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Sheet 2 of 2

Complete if Known	
Application Number	10/799325
Filing Date	Mar 12, 2004
First Named Inventor	Randy Hoffman
Art Unit	2811
Examiner Name	Thien Tran
Attorney Docket Number	200315134-1

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
TT		OHTA, H., "Frontier of transparent oxide semiconductors", Solid State Electronics, vol. 47, no. 12, Dec 2003, pgs 2261-2267	
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